



WBFBP-03B Plastic-Encapsulate Diodes

DK4148NND03 SWITCHING DIODE

DESCRIPTION

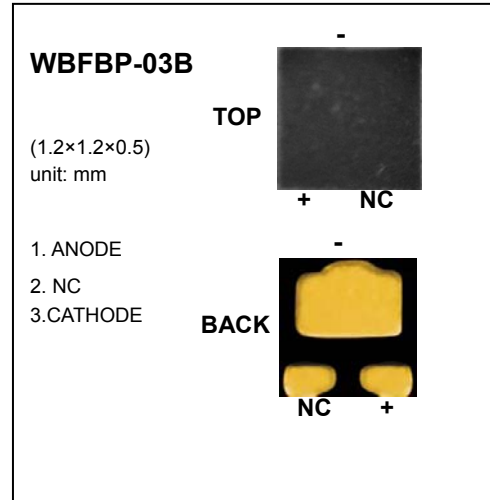
Epitaxial Planar Silicon Diode

FEATURES

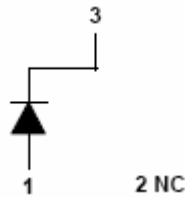
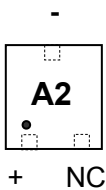
- Fast Switching Speed
- Ultra-Small Surface Mount Package
- For General Purpose Switching Applications
- High Conductance
- Lead Free Product

APPLICATION

High Conductance Ultra Fast Diode
 For Portable Equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)



MARKING: A2



Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Peak Reverse Voltage	V_{RRM}		
Working Peak Reverse Voltage	V_{RWM}	75	V
DC Blocking Voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Output Current	I_O	150	mA
Peak Forward Surge Current @t=1.0μs	I_{FSM}	2.0	A
@t = 1.0s		1.0	
Power Dissipation	P_D	150	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	833	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

Electrical Ratings @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Forward voltage	V _{F1}			0.715	V	I _F =1mA
	V _{F2}			0.855	V	I _F =10mA
	V _{F3}			1.0	V	I _F =50mA
	V _{F4}			1.25	V	I _F =150mA
Reverse current	I _{R1}			1	μA	V _R =75V
	I _{R2}			25	nA	V _R =20V
Capacitance between terminals	C _T			2	pF	V _R =0V, f=1MHz
Reverse recovery time	t _{rr}			4	ns	I _F =I _R =10mA I _{rr} =0.1X I _R , R _L =100Ω